

Hydrogen interaction with point defects in the Si-SiO₂ structures and its influence on the interface properties

Kropman, Daniel; Mellikov, Enn; Käerner, T.; Ugaste, Ülo; Laas, Tõnu; Heinmaa, I.; Abru, Uno; Medvid, A. Solid state phenomena 2008 / p. 345-350 <https://www.scientific.net/SSP.131-133.345>

Impurity interaction with point defects in the Si-SiO₂ structures and its influence on the interface properties

Kropman, Daniel; Mellikov, Enn; Käerner, T.; Ugaste, Ülo; Laas, Tõnu; Heinmaa, I.; Medvid, A. Materials science and engineering : B 2006 / p. 222-226 : ill <https://www.sciencedirect.com/science/article/pii/S0921510706004375>

Interaction between point defects in the Si-Si=2 system

Kropman, Daniel; Käerner, T.; Samoson, Ago; Heinmaa, I.; Mellikov, Enn Nuclear instruments & methods in physics research. Section B 2002 / p. 78-82 <https://www.sciencedirect.com/science/article/pii/S0168583X0100862X>

Interaction between point defects in the Si-SiO₂ system during the process of its formation

Kropman, Daniel; Käerner, T.; Samoson, Ago; Heidmaa, I.; Ugaste, Ülo; Mellikov, Enn Defect and Diffusion Forum 2001 / p. 1737-1744 <https://www.sciencedirect.com/science/article/abs/pii/S0168583X0100862X>

Interaction between point defects, extended defects and impurities in the Si-SiO₂ system during the process of its formation

Kropman, Daniel; Käerner, T.; Abru, Uno; Ugaste, Ülo; Mellikov, Enn Thin solid films 2004 / 1/2, p. 53-57 : ill <https://www.sciencedirect.com/science/article/abs/pii/S0921510704003459>

Interaction between point defects, extended defects and impurities in the Si-SiO₂ system during the process of its formation

Kropman, Daniel; Käerner, T.; Abru, Uno; Ugaste, Ülo; Mellikov, Enn; Kauk, Marit Materials science and engineering : B 2004 / p. 295-298 : ill <https://www.sciencedirect.com/science/article/abs/pii/S0921510704003459>

Interaction of point defects with impurities in the Si-SiO₂ system and its influence on the properties of the interface

Kropman, Daniel; Mellikov, Enn; Lott, Kalju; Käerner, T.; Heinmaa, I.; Laas, Tõnu; Medvid, A.; Skroupa, W.; Prucnal, S.; Zvyagin, S.; Cizmar, E.; Ozerov, M.; Wosnitsa, J. Solid state phenomena 2010 / p. 145-148 : ill <https://www.sciencedirect.com/science/article/abs/pii/S0040609009014564>

Interaction of point defects with impurities in the Si-SiO₂ system and its influence on the properties of the interface

Kropman, Daniel; Mellikov, Enn; Öpik, Andres; Lott, Kalju; Käerner, T.; Heinmaa, I.; Laas, Tõnu; Medvid, A.; Skroupa, W.; Prucnal, S.; Rebohle, L.; Zvyagin, S.; Cizmar, E.; Ozerov, M.; Wosnitsa, J. Thin solid films 2010 / 9, p. 2374-2376 <https://www.sciencedirect.com/science/article/abs/pii/S0040609009014564>

Interaction of point defects with impurities in the Si-SiO₂ system and its influence on the properties of the interface

Kropman, Daniel; Mellikov, Enn; Lott, Kalju; Käerner, T.; Heinmaa, I. Gettering and defect engineering in semiconductor technology XIII : CADEST 2009 : proceedings of the XIIIth International Autumn Meeting, Döllnsee-Schorfheide, north of Berlin, Germany, September 26 - October 02, 2009 2010 / p. 145-148 : ill <https://www.sciencedirect.com/science/article/abs/pii/S0040609009014564>

Interaktsioon punktdefektide ja lisandite vahel süsteemis Si-SiO₂ ja nende mõju piirpinna omadustele : [ettekande sisukokkuvõte]

Kropman, Daniel; Käerner, T.; Heinmaa, I. Eesti Füüsika Seltsi aastaraamat 2008 2009 / lk. 119-120

Investigation of strain relaxation mechanism in Si-SiO₂ system during the process of its formation

Kropman, Daniel; Poll, V.; Käerner, T.; Ugaste, Ülo; Mellikov, Enn; Arbu, Uno; Paomets, V. Physica status solidi (a) 2003 / 2, p. 297-301 <https://onlinelibrary.wiley.com/doi/abs/10.1002/pssa.200306611>

Point defects interaction with extended defects and impurities and its influence on the Si-SiO₂ system properties

Kropman, Daniel; Arbu, Uno; Käerner, T.; Ugaste, Ülo; Mellikov, Enn; Kauk, Marit; Heinmaa, I.; Samoson, Ago; Medvid, A. Gettering and defect engineering in semiconductor technology. XI 2005 / p. 333-338 : ill https://www.researchgate.net/publication/243760197_Point_Defects_Interaction_with_Extended_Defects_and_Impurities_and_Its_Influence_on_the_Si-SiO_2_System_Properties

Point defects interaction with extended defects in the Si-SiO₂ system [Electronic resource]

Kropman, Daniel; Käerner, T.; Abru, Uno; Ugaste, Ülo; Mellikov, Enn Proceedings IVC-16 : Venice, 2004 2004 / p. SS1-TuP394 [CD-ROM] https://www.researchgate.net/publication/243760197_Point_Defects_Interaction_with_Extended_Defects_and_Impurities_and_Its_Influence_on_the_Si-SiO_2_System_Properties

Strain relaxation mechanism in the Si-SiO₂ system and its influence on the interface properties

Kropman, Daniel; Mellikov, Enn; Öpik, Andres; Lott, Kalju; Volobujeva, Olga; Käerner, T.; Heinmaa, I.; Laas, Tõnu; Medvid, A. Radiation Interaction with Materials and its use in Technologies : Kaunas, 24-27.09.2008 2008 / p. 204-207 <https://www.sciencedirect.com/science/article/pii/S0921452609010321>

Strain relaxation mechanism in the Si-SiO₂ system and its influence on the interface properties

